

Abstract of the Disclosure

A base contact section of a planar structure electrically connecting a base electrode to a base region of a bipolar transistor is constructed of a repeating structure in a plan view, in which a high impurity concentration region of the same conductivity type as that of the base region and a region of the reverse conductivity type from that of the base region or low concentration region of the same conductivity type as that of the base region, arranged in an alternately manner starting with a high impurity concentration region of the same conductivity type as that of the base region from an emitter region side. With such a structure, accumulation of minor carriers in the base contact section can be suppressed, a high switching speed can be achieved and reduction in power consumption can be realized. Further, the emitter region is formed in a configuration of a plurality of stripes and the base region to which a base electrode is not connected is formed in each of the emitter regions of a stripe pattern, thereby enabling not only a junction area between the emitter regions and the base region to be increased with no space for the base electrode provided but also a safe operation area to be wider.

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